

**General Description**

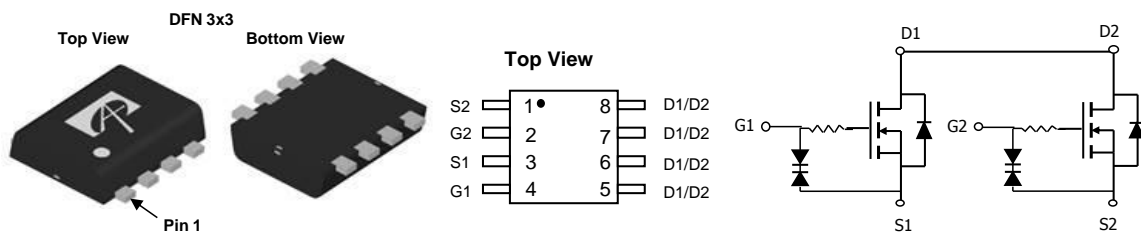
- Trench Power  $\alpha$ MOS™ LV technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- ESD protection
- RoHS and Halogen-Free Compliant

**Applications**

- Battery protection switch
- Mobile device battery charging and discharging

**Product Summary**

$V_{DS}$	24V
$I_D$ (at $V_{GS}=4.5V$ )	8A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 13.5m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=4.0V$ )	< 14m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=3.7V$ )	< 15m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=3.1V$ )	< 17m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=2.5V$ )	< 21m $\Omega$

**Typical ESD protection**
**HBM Class 2**


Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON3818	DFN 3x3	Tape & Reel	3000

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	24	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>G</sup>	$I_D$	$T_A=25^\circ\text{C}$	8
		$T_A=70^\circ\text{C}$	6
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	32	A
Power Dissipation <sup>B</sup>	$P_D$	$T_A=25^\circ\text{C}$	2.7
		$T_A=70^\circ\text{C}$	1.7
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	35	45	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A,D</sup>				
Maximum Junction-to-Lead	$R_{\theta JL}$	15	20	$^\circ\text{C/W}$

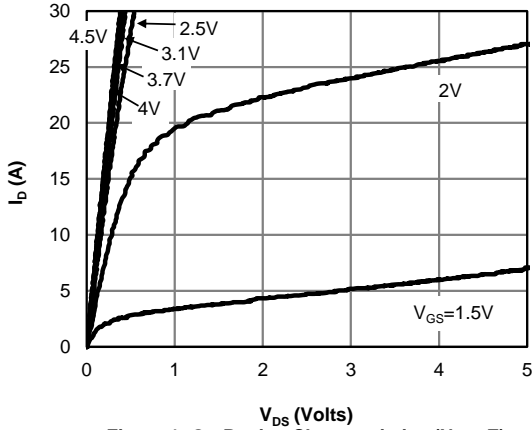
**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	24			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.8	1.2	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A T <sub>J</sub> =125°C	7.5	10.8	13.5	mΩ
		V <sub>GS</sub> =4.0V, I <sub>D</sub> =6A	7.8	11.2	14	
		V <sub>GS</sub> =3.7V, I <sub>D</sub> =6A	8	11.5	15	
		V <sub>GS</sub> =3.1V, I <sub>D</sub> =4A	8	12.5	17	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	8.6	14.8	21	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =8A		42		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.66	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =12V, f=1MHz		840		pF
C <sub>oss</sub>	Output Capacitance			210		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			205		pF
R <sub>g</sub>	Gate resistance	f=1MHz		2		kΩ
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =12V, I <sub>D</sub> =8A		9.5	15	nC
Q <sub>gs</sub>	Gate Source Charge			1.5		nC
Q <sub>gd</sub>	Gate Drain Charge			4.5		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =12V, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		0.3		μs
t <sub>r</sub>	Turn-On Rise Time			0.8		μs
t <sub>D(off)</sub>	Turn-Off DelayTime			1.7		μs
t <sub>f</sub>	Turn-Off Fall Time			5.2		μs

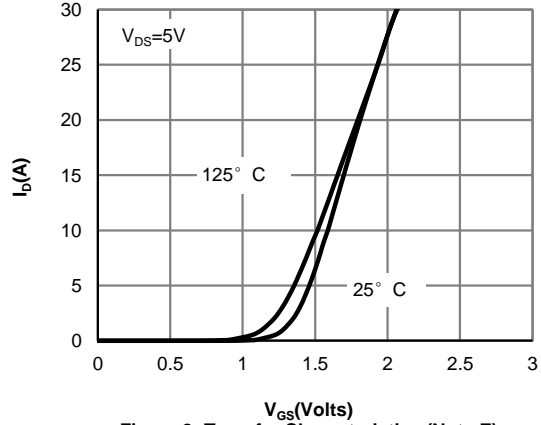
- A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.
- C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.
- D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

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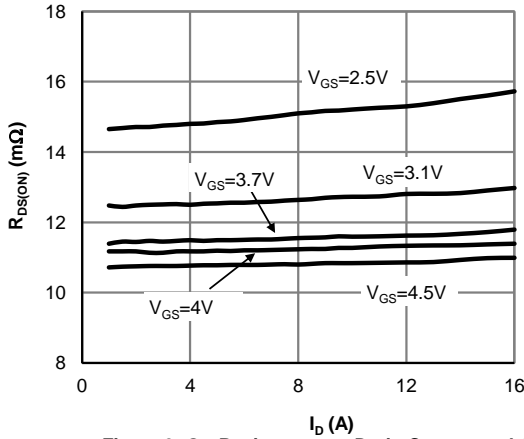
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



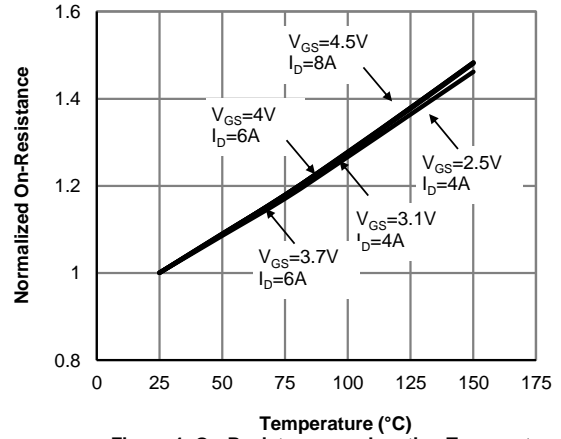
**Figure 1: On-Region Characteristics (Note E)**



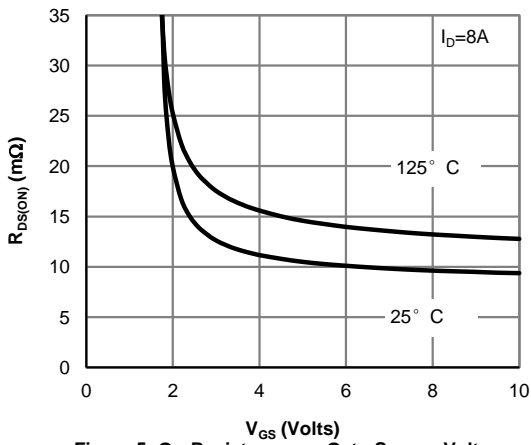
**Figure 2: Transfer Characteristics (Note E)**



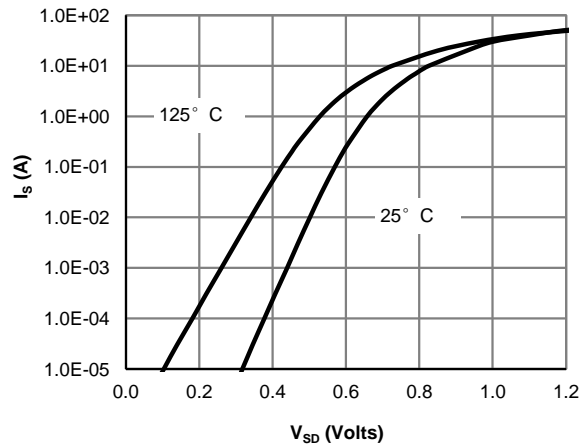
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

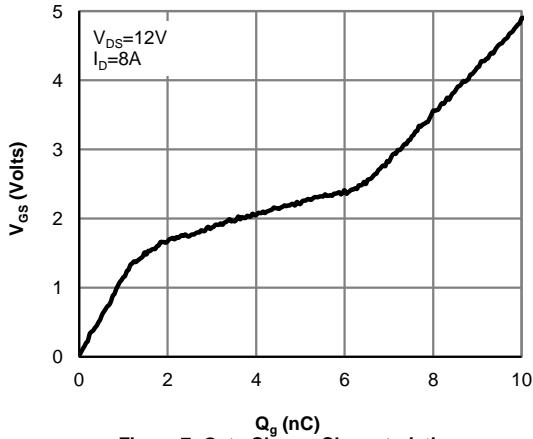


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

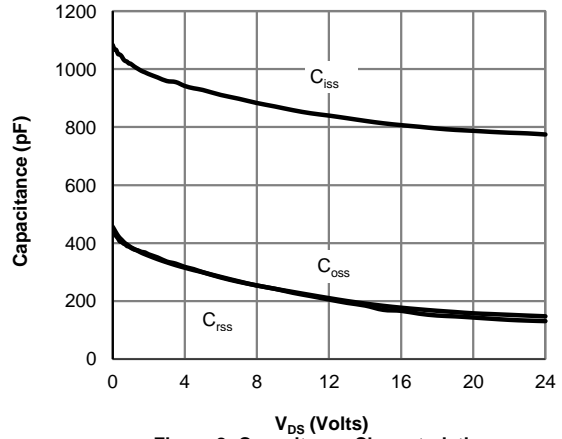


**Figure 6: Body-Diode Characteristics (Note E)**

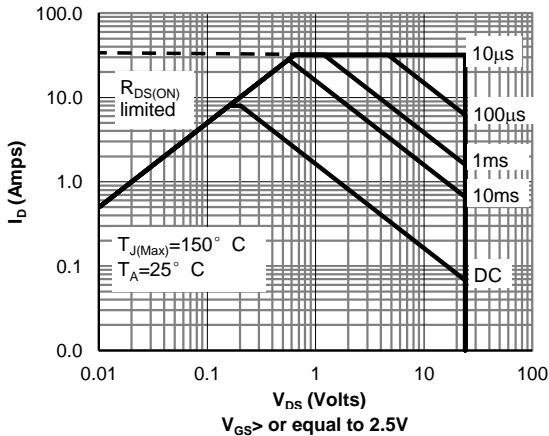
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



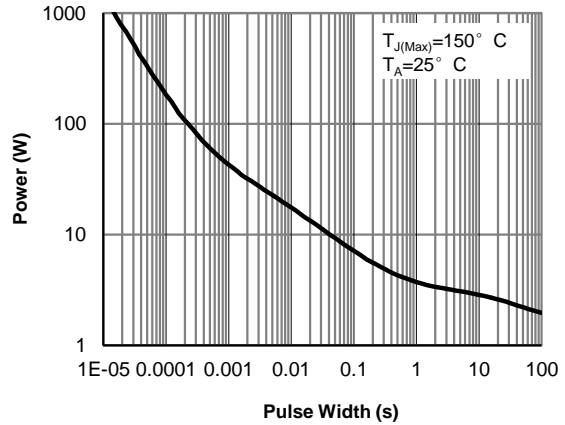
**Figure 7: Gate-Charge Characteristics**



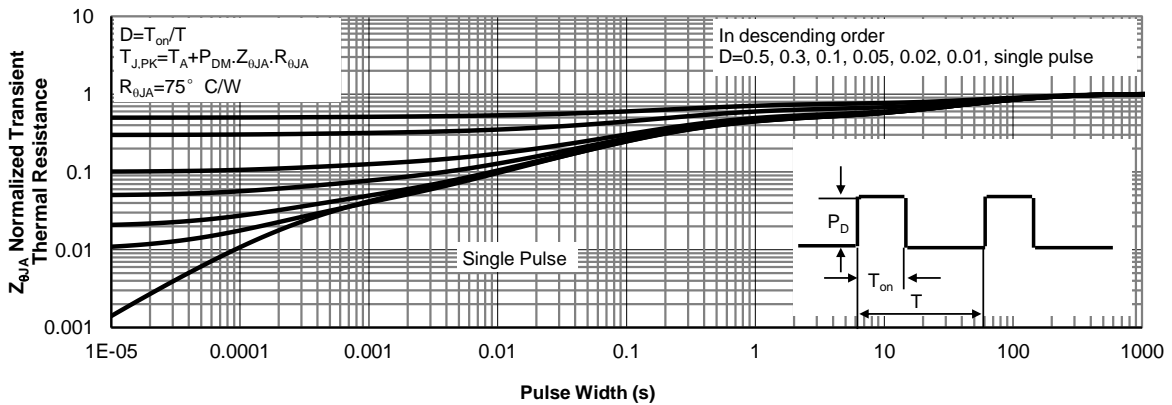
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

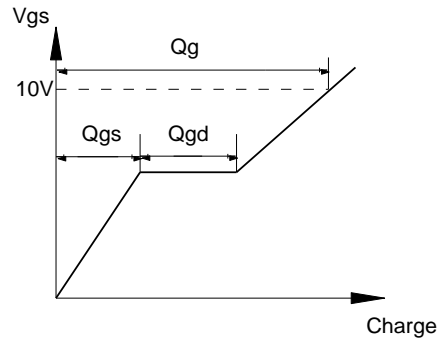
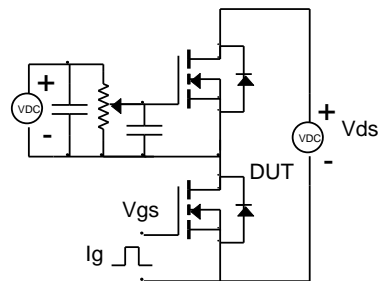


**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)**

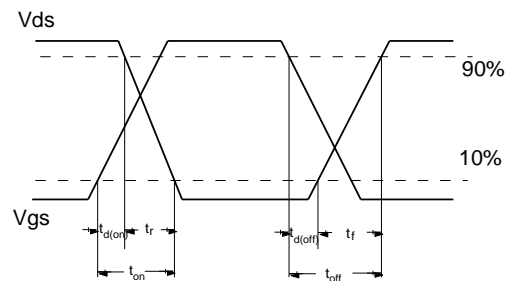
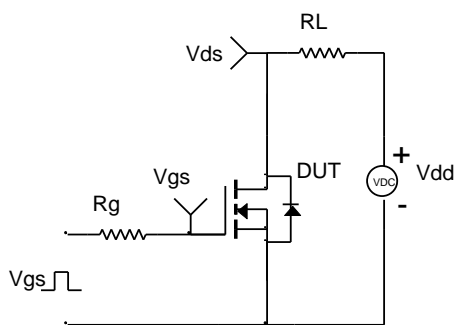


**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

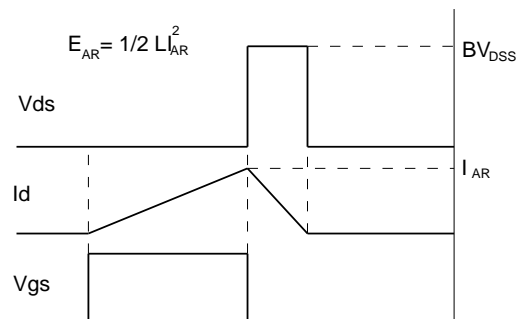
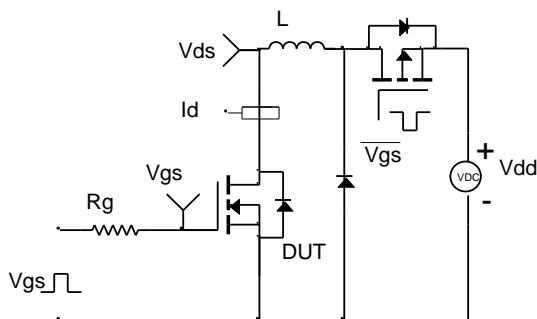
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

